



Is Now Part of



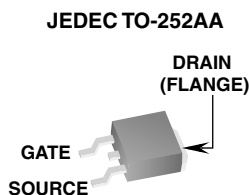
**ON Semiconductor®**

To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

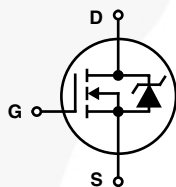
ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

**N-Channel Logic Level UltraFET Power MOSFET**  
**60 V, 11 A, 107 mΩ**

**Packaging**



**Symbol**



**Features**

- Ultra Low On-Resistance
  - $r_{DS(ON)} = 0.092\Omega, V_{GS} = 10V$
  - $r_{DS(ON)} = 0.107\Omega, V_{GS} = 5V$
- Simulation Models
  - Temperature Compensated PSPICE® and SABER™ Electrical Models
  - Spice and SABER Thermal Impedance Models
  - www.fairchildsemi.com
- Peak Current vs Pulse Width Curve
- UIS Rating Curve
- Switching Time vs  $R_{GS}$  Curves

**Ordering Information**

PART NUMBER	PACKAGE	BRAND
HUF76407D3ST	TO-252AA	76407D

**Absolute Maximum Ratings**  $T_C = 25^\circ C$ , Unless Otherwise Specified

	HUF76407D3ST	UNITS
Drain to Source Voltage (Note 1) . . . . .	$V_{DSS}$	60 V
Drain to Gate Voltage ( $R_{GS} = 20k\Omega$ ) (Note 1) . . . . .	$V_{DGR}$	60 V
Gate to Source Voltage . . . . .	$V_{GS}$	$\pm 16$ V
Drain Current		
Continuous ( $T_C = 25^\circ C, V_{GS} = 5V$ ) . . . . .	$I_D$	11 A
Continuous ( $T_C = 25^\circ C, V_{GS} = 10V$ ) (Figure 2) . . . . .	$I_D$	12 A
Continuous ( $T_C = 135^\circ C, V_{GS} = 5V$ ) . . . . .	$I_D$	6 A
Continuous ( $T_C = 135^\circ C, V_{GS} = 4.5V$ ) (Figure 2) . . . . .	$I_D$	6 A
Pulsed Drain Current . . . . .	$I_{DM}$	Figure 4
Pulsed Avalanche Rating . . . . .	.UIS	Figures 6, 14, 15
Power Dissipation . . . . .	$P_D$	38 W
Derate Above $25^\circ C$ . . . . .		0.25 W/ $^\circ C$
Operating and Storage Temperature . . . . .	$T_J, T_{STG}$	-55 to 175 $^\circ C$
Maximum Temperature for Soldering		
Leads at 0.063in (1.6mm) from Case for 10s . . . . .	$T_L$	300 $^\circ C$
Package Body for 10s, See Techbrief TB334 . . . . .	$T_{pkg}$	260 $^\circ C$

NOTE:

1.  $T_J = 25^\circ C$  to  $150^\circ C$ .

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

For severe environments, see our Automotive HUFA series.

# HUF76407D3S

## Electrical Specifications $T_C = 25^\circ\text{C}$ , Unless Otherwise Specified

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS	
<b>OFF STATE SPECIFICATIONS</b>							
Drain to Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ (Figure 12)	60	-	-	V	
		$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$ , $T_C = -40^\circ\text{C}$ (Figure 12)	55	-	-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 55\text{V}$ , $V_{GS} = 0\text{V}$	-	-	1	$\mu\text{A}$	
		$V_{DS} = 50\text{V}$ , $V_{GS} = 0\text{V}$ , $T_C = 150^\circ\text{C}$	-	-	250	$\mu\text{A}$	
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 16\text{V}$	-	-	$\pm 100$	nA	
<b>ON STATE SPECIFICATIONS</b>							
Gate to Source Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}$ , $I_D = 250\mu\text{A}$ (Figure 11)	1	-	3	V	
Drain to Source On Resistance	$r_{DS(ON)}$	$I_D = 13\text{A}$ , $V_{GS} = 10\text{V}$ (Figures 9, 10)	-	0.077	0.092	$\Omega$	
		$I_D = 8\text{A}$ , $V_{GS} = 5\text{V}$ (Figure 9)	-	0.095	0.107	$\Omega$	
		$I_D = 8\text{A}$ , $V_{GS} = 4.5\text{V}$ (Figure 9)	-	0.107	0.117	$\Omega$	
<b>THERMAL SPECIFICATIONS</b>							
Thermal Resistance Junction to Case	$R_{\theta JC}$	TO-252	-	-	3.94	$^\circ\text{C/W}$	
Thermal Resistance Junction to Ambient	$R_{\theta JA}$		-	-	100	$^\circ\text{C/W}$	
<b>SWITCHING SPECIFICATIONS (<math>V_{GS} = 4.5\text{V}</math>)</b>							
Turn-On Time	$t_{ON}$	$V_{DD} = 30\text{V}$ , $I_D = 8\text{A}$ $V_{GS} = 4.5\text{V}$ , $R_{GS} = 32\Omega$ (Figures 15, 21, 22)	-	-	170	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	8	-	ns	
Rise Time	$t_r$		-	105	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	22	-	ns	
Fall Time	$t_f$		-	39	-	ns	
Turn-Off Time	$t_{OFF}$		-	-	92	ns	
<b>SWITCHING SPECIFICATIONS (<math>V_{GS} = 10\text{V}</math>)</b>							
Turn-On Time	$t_{ON}$	$V_{DD} = 30\text{V}$ , $I_D = 13\text{A}$ $V_{GS} = 10\text{V}$ , $R_{GS} = 32\Omega$ (Figures 16, 21, 22)	-	-	56	ns	
Turn-On Delay Time	$t_{d(ON)}$		-	5	-	ns	
Rise Time	$t_r$		-	32	-	ns	
Turn-Off Delay Time	$t_{d(OFF)}$		-	43	-	ns	
Fall Time	$t_f$		-	45	-	ns	
Turn-Off Time	$t_{OFF}$		-	-	132	ns	
<b>GATE CHARGE SPECIFICATIONS</b>							
Total Gate Charge	$Q_{g(TOT)}$	$V_{GS} = 0\text{V}$ to $10\text{V}$	$V_{DD} = 30\text{V}$ , $I_D = 8\text{A}$ , $I_{g(REF)} = 1.0\text{mA}$ (Figures 14, 19, 20)	-	9.4	11.3	nC
Gate Charge at 5V	$Q_{g(5)}$	$V_{GS} = 0\text{V}$ to $5\text{V}$		-	5.2	6.2	nC
Threshold Gate Charge	$Q_{g(TH)}$	$V_{GS} = 0\text{V}$ to $1\text{V}$		-	0.36	0.43	nC
Gate to Source Gate Charge	$Q_{gs}$			-	1.2	-	nC
Reverse Transfer Capacitance	$Q_{gd}$			-	2.5	-	nC
<b>CAPACITANCE SPECIFICATIONS</b>							
Input Capacitance	$C_{ISS}$	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$ (Figure 13)	-	350	-	pF	
Output Capacitance	$C_{OSS}$		-	105	-	pF	
Reverse Transfer Capacitance	$C_{RSS}$		-	23	-	pF	

## Source to Drain Diode Specifications

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Source to Drain Diode Voltage	$V_{SD}$	$I_{SD} = 8\text{A}$	-	-	1.25	V
		$I_{SD} = 3\text{A}$	-	-	1.0	V
Reverse Recovery Time	$t_{rr}$	$I_{SD} = 8\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	66	ns
Reverse Recovered Charge	$Q_{RR}$	$I_{SD} = 8\text{A}$ , $dI_{SD}/dt = 100\text{A}/\mu\text{s}$	-	-	159	nC

Typical Performance Curves

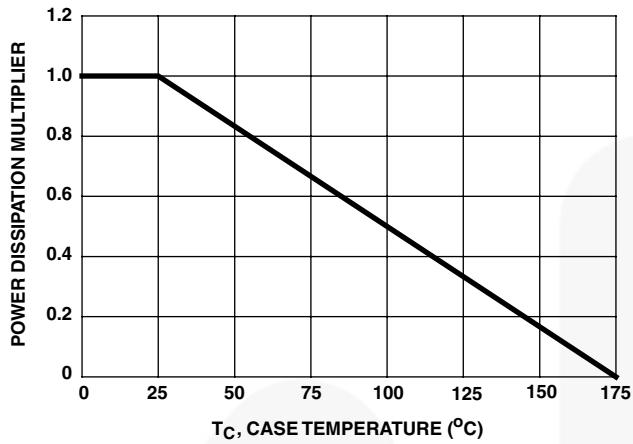


FIGURE 1. NORMALIZED POWER DISSIPATION vs CASE TEMPERATURE

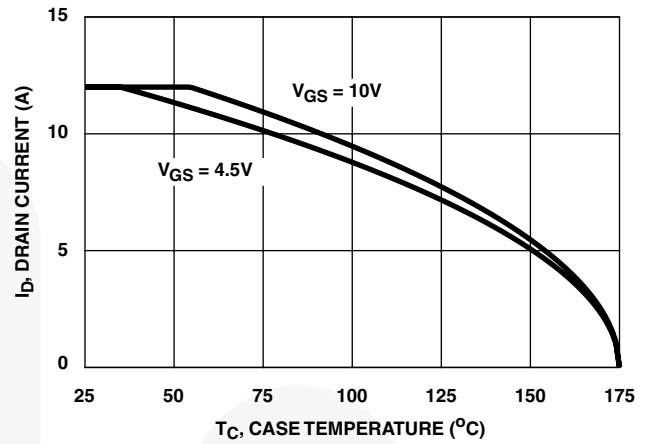


FIGURE 2. MAXIMUM CONTINUOUS DRAIN CURRENT vs CASE TEMPERATURE

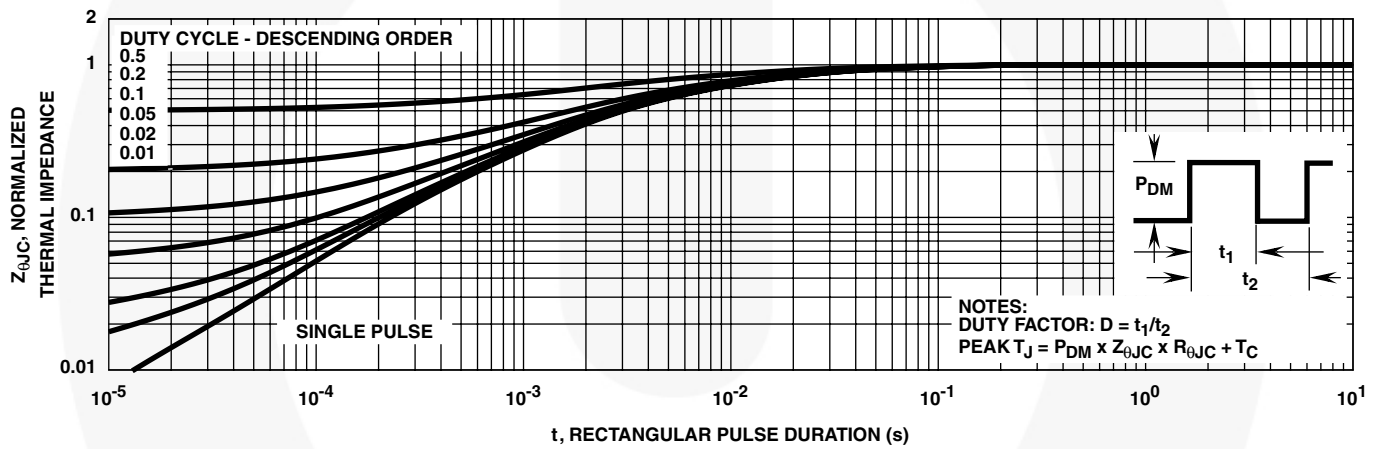


FIGURE 3. NORMALIZED MAXIMUM TRANSIENT THERMAL IMPEDANCE

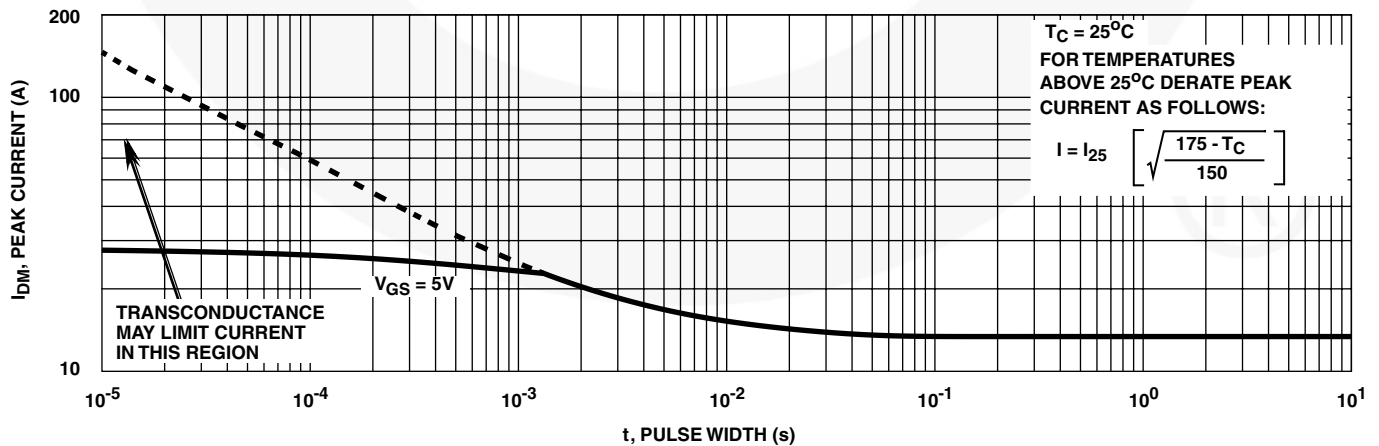


FIGURE 4. PEAK CURRENT CAPABILITY

Typical Performance Curves (Continued)

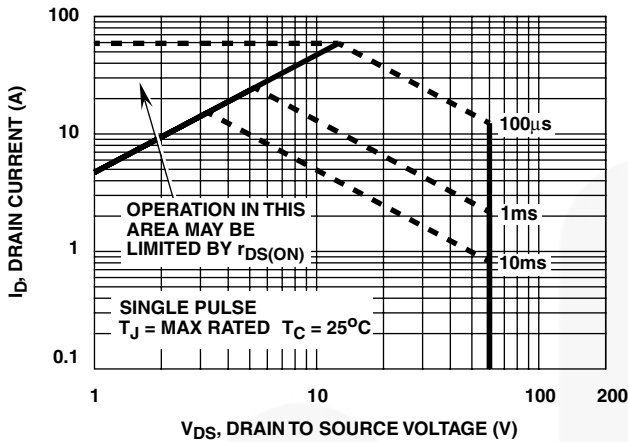
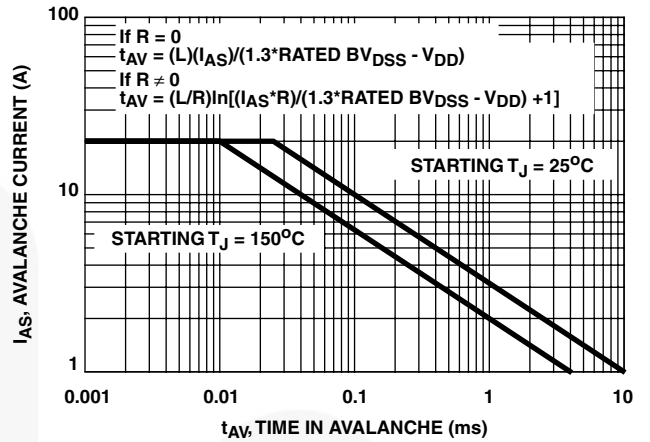


FIGURE 5. FORWARD BIAS SAFE OPERATING AREA



NOTE: Refer to Fairchild Application Notes AN9321 and AN9322.

FIGURE 6. UNCLAMPED INDUCTIVE SWITCHING CAPABILITY

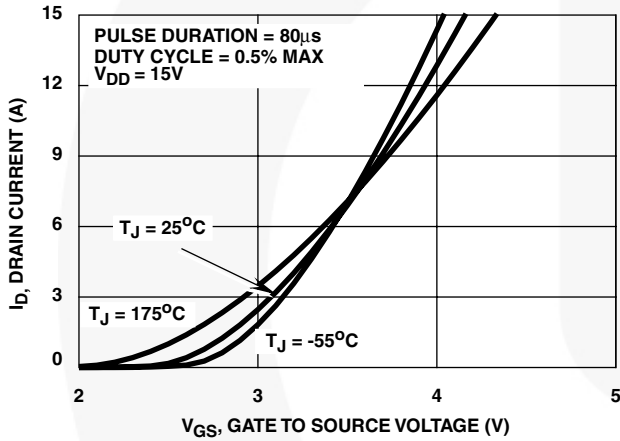


FIGURE 7. TRANSFER CHARACTERISTICS

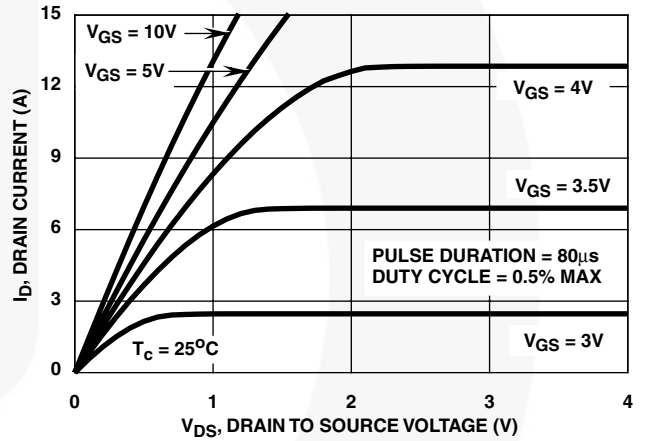


FIGURE 8. SATURATION CHARACTERISTICS

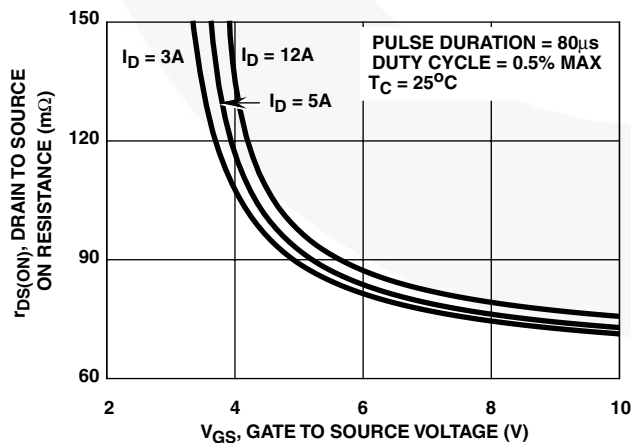


FIGURE 9. DRAIN TO SOURCE ON RESISTANCE vs. GATE VOLTAGE AND DRAIN CURRENT

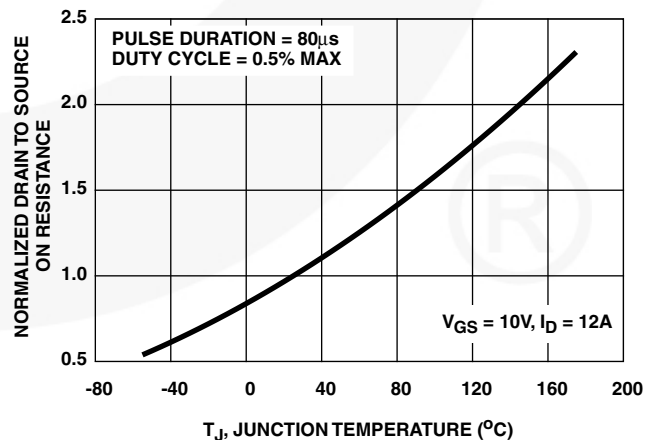


FIGURE 10. NORMALIZED DRAIN TO SOURCE ON RESISTANCE vs. JUNCTION TEMPERATURE

Typical Performance Curves (Continued)

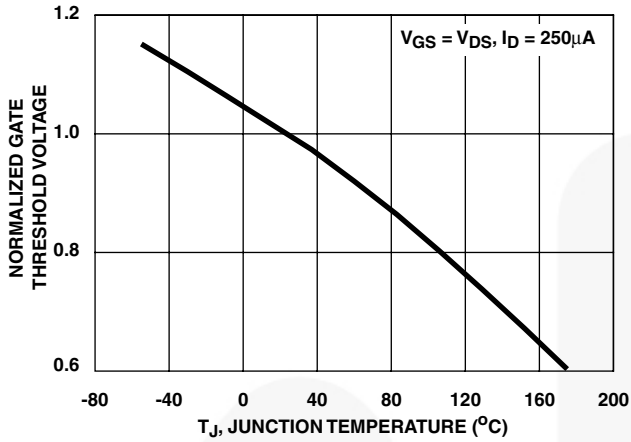


FIGURE 11. NORMALIZED GATE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

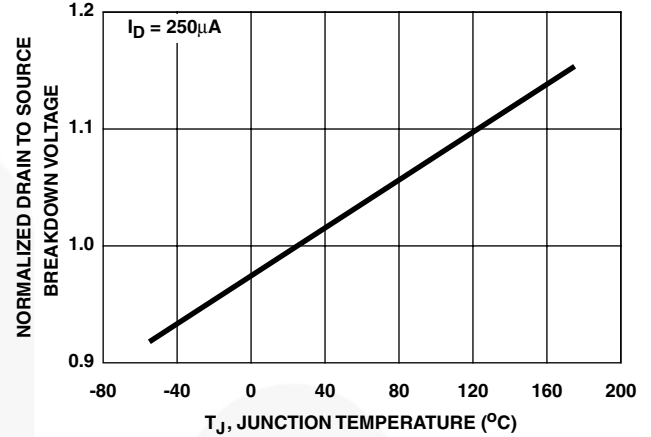


FIGURE 12. NORMALIZED DRAIN TO SOURCE BREAKDOWN VOLTAGE vs JUNCTION TEMPERATURE

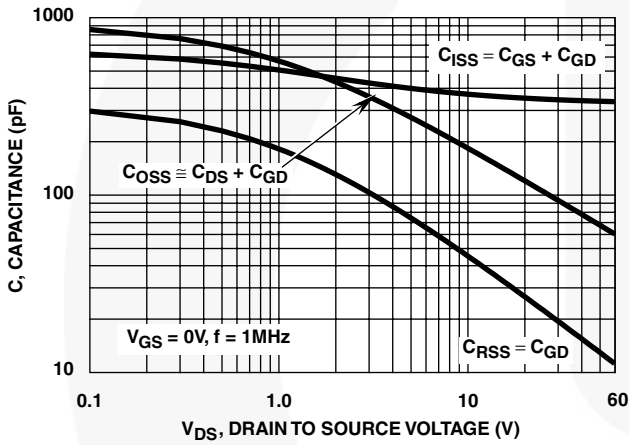
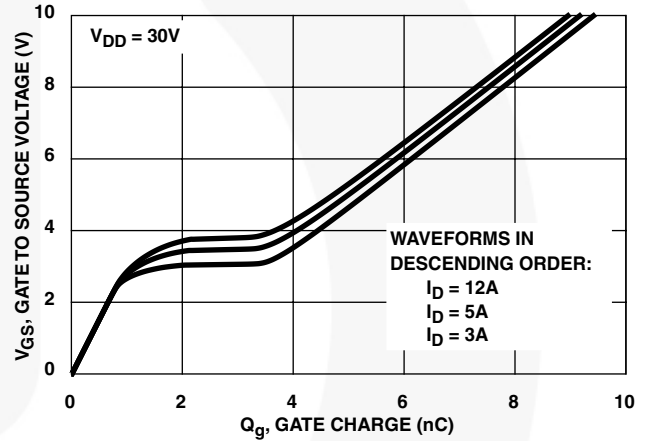


FIGURE 13. CAPACITANCE vs DRAIN TO SOURCE VOLTAGE



NOTE: Refer to Fairchild Application Notes AN7254 and AN7260.

FIGURE 14. GATE CHARGE WAVEFORMS FOR CONSTANT GATE CURRENT

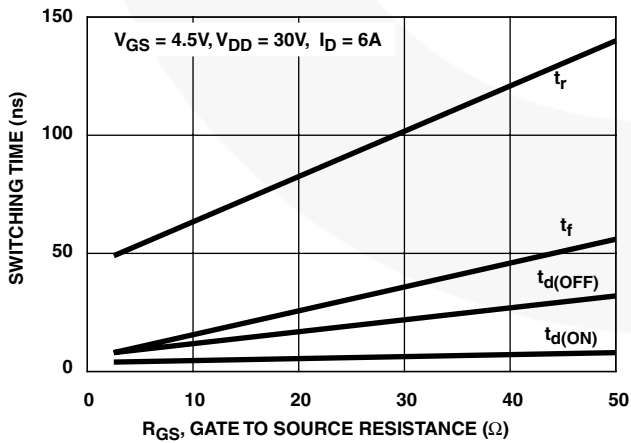


FIGURE 15. SWITCHING TIME vs GATE RESISTANCE

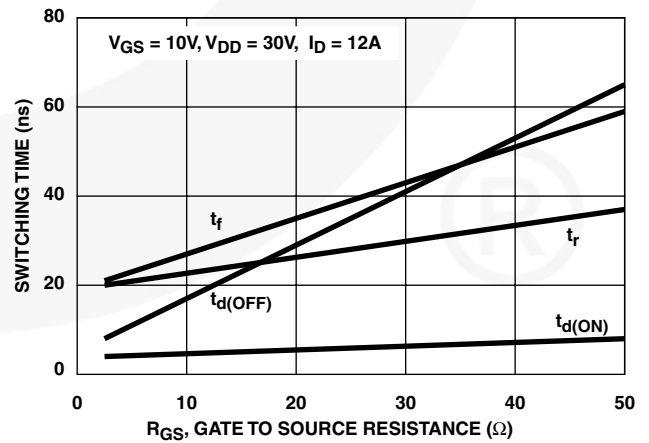


FIGURE 16. SWITCHING TIME vs GATE RESISTANCE

Test Circuits and Waveforms

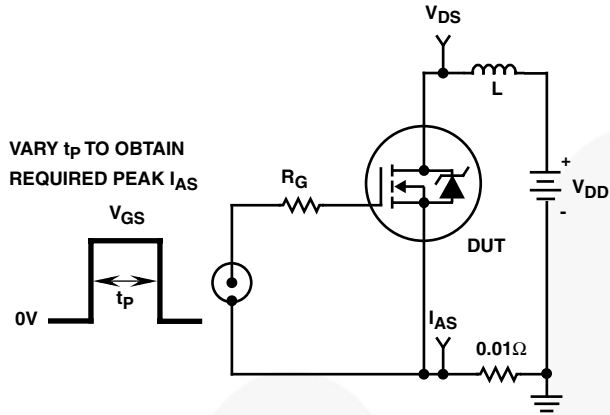


FIGURE 17. UNCLAMPED ENERGY TEST CIRCUIT

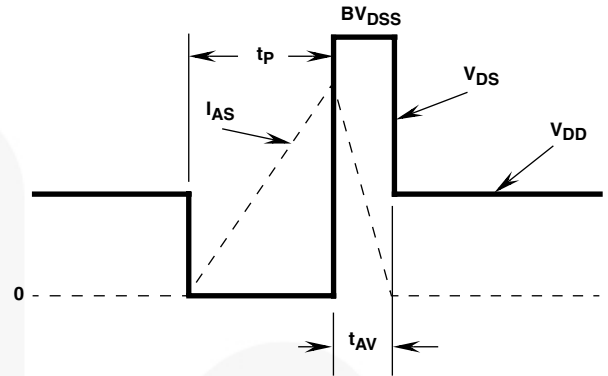


FIGURE 18. UNCLAMPED ENERGY WAVEFORMS

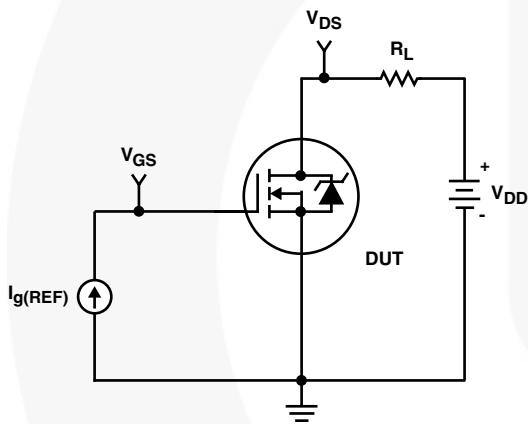


FIGURE 19. GATE CHARGE TEST CIRCUIT

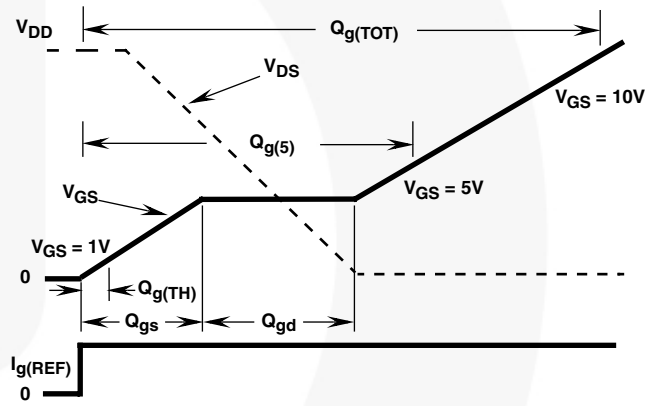


FIGURE 20. GATE CHARGE WAVEFORMS

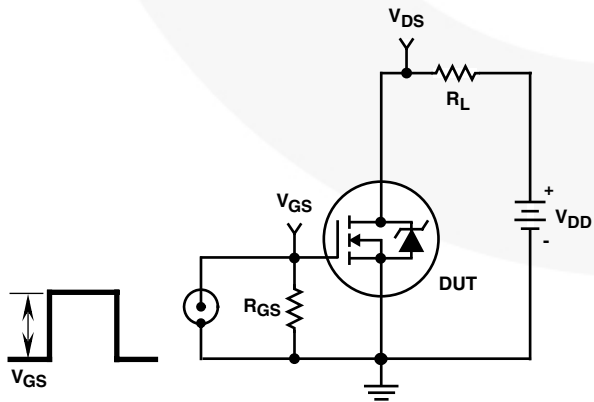


FIGURE 21. SWITCHING TIME TEST CIRCUIT

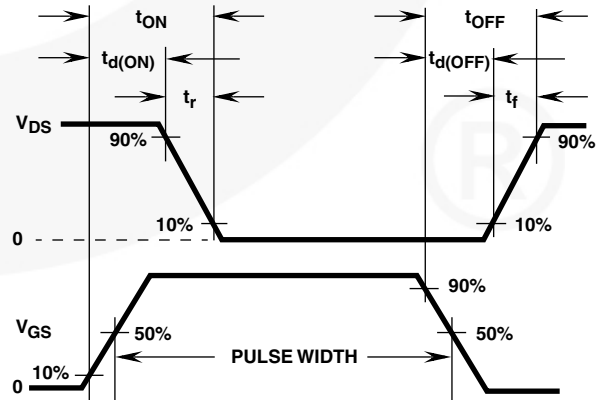


FIGURE 22. SWITCHING TIME WAVEFORM

# HUF76407D3S

## PSPICE Electrical Model

.SUBCKT HUF76407 2 1 3 ; rev 28June 1999

CA 12 8 3.9e-9  
 CB 15 14 4.9e-9  
 CIN 6 8 3.25e-10

DBODY 7 5 DBODYMOD  
 DBREAK 5 11 DBREAKMOD  
 DPLCAP 10 5 DPLCAPMOD

EBREAK 11 7 17 18 67.8  
 EDS 14 8 5 8 1  
 EGS 13 8 6 8 1  
 ESG 6 10 6 8 1  
 EVTHRES 6 21 19 8 1  
 EVTEMP 20 6 18 22 1

IT 8 17 1

LDRAIN 2 5 1.0e-9  
 LGATE 1 9 5.42e-9  
 LSOURCE 3 7 2.57e-9

MMED 16 6 8 8 MMEDMOD  
 MSTRO 16 6 8 8 MSTROMOD  
 MWEAK 16 21 8 8 MWEAKMOD

RBREAK 17 18 RBREAKMOD 1  
 RDRAIN 50 16 RDRAINMOD 3.7e-2  
 RGATE 9 20 3.37  
 RLDRAIN 2 5 10  
 RLGATE 1 9 54.2  
 RLSOURCE 3 7 25.7  
 RSLC1 5 51 RSLCMOD 1e-6  
 RSLC2 5 50 1e3  
 RSOURCE 8 7 RSOURCEMOD 2.50e-2  
 RVTHRES 22 8 RVTHRESMOD 1  
 RVTEMP 18 19 RVTEMPMOD 1

S1A 6 12 13 8 S1AMOD  
 S1B 13 12 13 8 S1BMOD  
 S2A 6 15 14 13 S2AMOD  
 S2B 13 15 14 13 S2BMOD

VBAT 22 19 DC 1

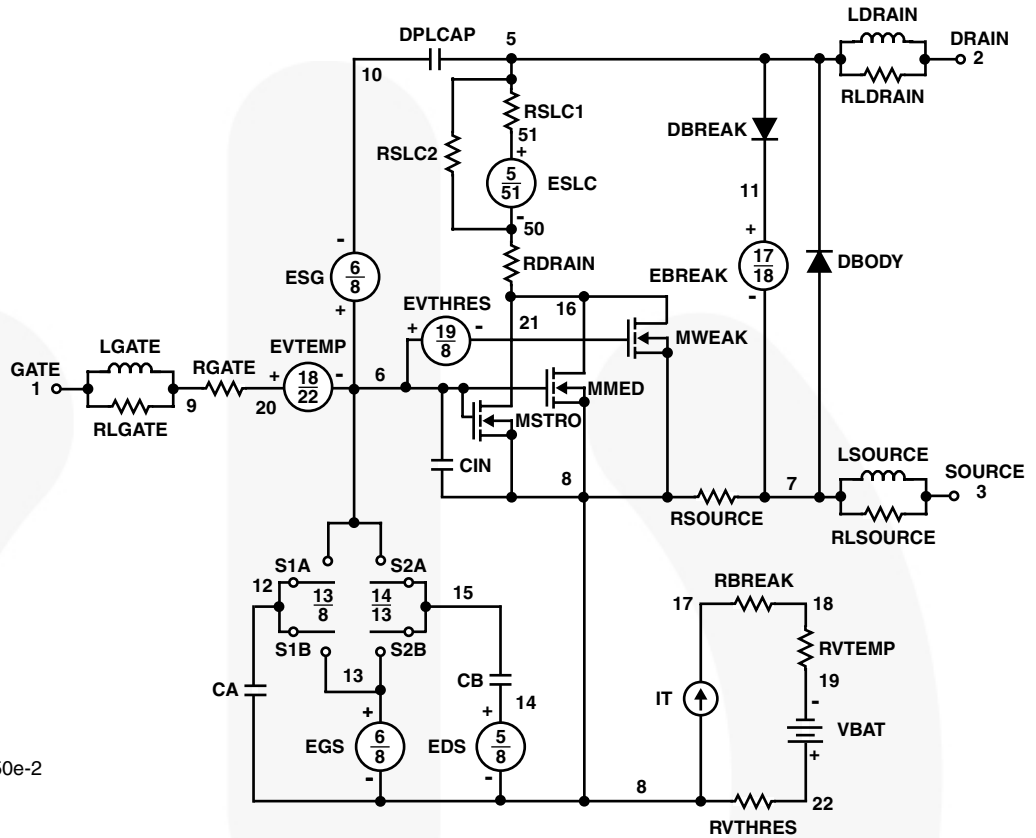
ESLC 51 50 VALUE={(V(5,51)/ABS(V(5,51)))\*(PWR(V(5,51)/(1e-6\*30),3))}

.MODEL DBODYMOD D (IS = 1.75e-13 RS = 1.75e-2 TRS1 = 1e-4 TRS2 = 5e-6 CJO = 5.9e-10 TT = 5.45e-8 N = 1.03 M = 0.6)  
 .MODEL DBREAKMOD D (RS = 6.50e-1 TRS1 = 1.25e-4 TRS2 = 1.34e-6)  
 .MODEL DPLCAPMOD D (CJO = 3.21e-10 IS = 1e-30 N = 10 M = 0.81)  
 .MODEL MMEDMOD NMOS (VTO = 2.02 KP = .83 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 3.37)  
 .MODEL MSTROMOD NMOS (VTO = 2.39 KP = 14 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u)  
 .MODEL MWEAKMOD NMOS (VTO = 1.78 KP = 0.02 IS = 1e-30 N = 10 TOX = 1 L = 1u W = 1u RG = 33.7 RS = 0.1)  
 .MODEL RBREAKMOD RES (TC1 = 1.06e-3 TC2 = 0)  
 .MODEL RDRAINMOD RES (TC1 = 1.23e-2 TC2 = 2.58e-5)  
 .MODEL RSLCMOD RES (TC1 = 0 TC2 = 0)  
 .MODEL RSOURCEMOD RES (TC1 = 1e-3 TC2 = 0)  
 .MODEL RVTHRESMOD RES (TC1 = -2.19e-3 TC2 = -4.97e-6)  
 .MODEL RVTEMPMOD RES (TC1 = -1.6e-3 TC2 = 1e-7)

.MODEL S1AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -4 VOFF = -2.5)  
 .MODEL S1BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -2.5 VOFF = -4)  
 .MODEL S2AMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = -0.5 VOFF = 0)  
 .MODEL S2BMOD VSWITCH (RON = 1e-5 ROFF = 0.1 VON = 0 VOFF = -0.5)

.ENDS

NOTE: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.







**SPICE Thermal Model**

REV 28June 1999

HUF76407T

CTHERM1 th 6 4.5e-4  
 CTHERM2 6 5 2.5e-3  
 CTHERM3 5 4 1.9e-3  
 CTHERM4 4 3 2.6e-3  
 CTHERM5 3 2 5.5e-3  
 CTHERM6 2 tl 1.8e-2

RTHERM1 th 6 3.1e-2  
 RTHERM2 6 5 15.1e-2  
 RTHERM3 5 4 4.2e-1  
 RTHERM4 4 3 8.4e-1  
 RTHERM5 3 2 8.7e-1  
 RTHERM6 2 tl 1.5

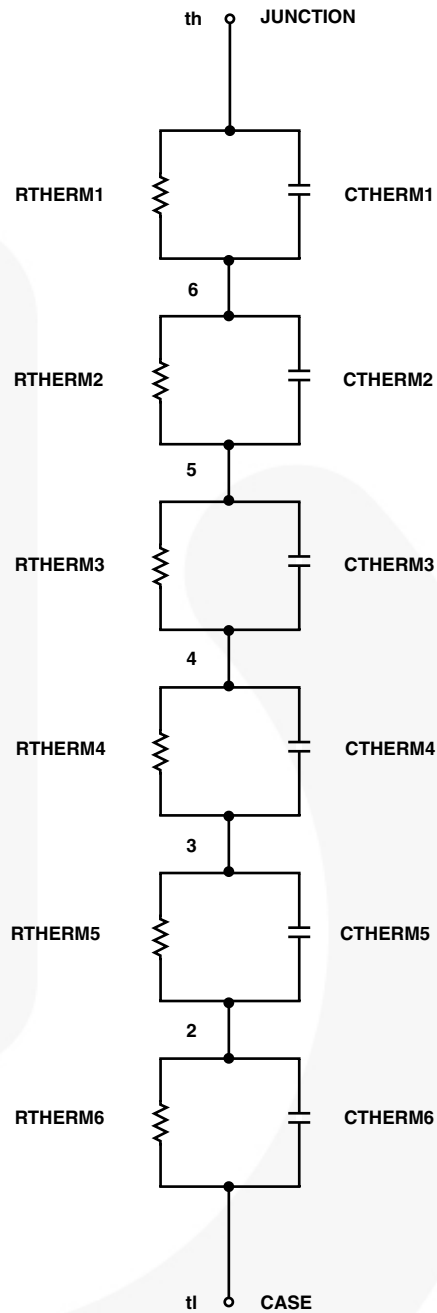
**SABER Thermal Model**

SABER thermal model HUF76407T

template thermal\_model th tl  
 thermal\_c th, tl

```
{
ctherm.ctherm1 th 6 = 4.5e-4
ctherm.ctherm2 6 5 = 2.5e-3
ctherm.ctherm3 5 4 = 1.9e-3
ctherm.ctherm4 4 3 = 2.6e-3
ctherm.ctherm5 3 2 = 5.5e-3
ctherm.ctherm6 2 tl = 1.8e-2
```



```
rtherm.rtherm1 th 6 = 3.1e-2
rtherm.rtherm2 6 5 = 15.1e-2
rtherm.rtherm3 5 4 = 4.2e-1
rtherm.rtherm4 4 3 = 8.4e-1
rtherm.rtherm5 3 2 = 8.7e-1
rtherm.rtherm6 2 tl = 1.5
}
```





**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- |   |   |                                       |   |
|---|---|---------------------------------------|---|
| AccuPower™  | F-PFS™  | PowerTrench®                          | Sync-Lock™  |
| AX-CAP®*  | FRFET®  | PowerXS™                              | SYSTEM GENERAL®*  |
| BitSiC™   | Global Power ResourceSM                         | Programmable Active Droop™            | TinyBoost®  |
| Build it Now™   | GreenBridge™                                    | QFET®                                 | TinyBuck®   |
| CorePLUS™   | Green FPS™                                      | QS™                                   | TinyCalc™   |
| CorePOWER™  | Green FPS™ e-Series™                            | Quiet Series™                         | TinyLogic®  |
| CROSSVOLT™  | Gmax™   | RapidConfigure™                       | TINYOPTO™   |
| CTL™  | GTO™  | Saving our world, 1mW/W/kW at a time™ | TinyPower™  |
| Current Transfer Logic™   | IntelliMAX™                                     | SignalWise™                           | TinyPWM™  |
| DEUXPEED®   | ISOPLANAR™                                      | SmartMax™                             | TinyWire™   |
| Dual Cool™  | Marking Small Speakers Sound Louder and Better™ | SMART START™                          | TranSiC™  |
| EcoSPARK®   | MegaBuck™                                       | Solutions for Your Success™           | TriFault Detect™  |
| EfficientMax™   | MICROCOUPLER™                                   | SPM®                                  | TRUECURRENT®*   |
| ESBC™   | MicroFET™                                       | STEALTH™                              | µSerDes™  |
|  | MicroPak™                                       | SuperFET®                             |  |
| Fairchild®  | MicroPak2™                                      | SuperSOT™-3                           | UHC®  |
| Fairchild Semiconductor®  | MillerDrive™                                    | SuperSOT™-6                           | Ultra FRFET™  |
| FACT Quiet Series™  | MotionMax™                                      | SuperSOT™-8                           | UniFET™   |
| FACT®   | mWSave®   | SupreMOS®                             | VCX™  |
| FAST®   | OptoHiT™  | SyncFET™                              | VisualMax™  |
| FastvCore™  | OPTOLOGIC®                                      |                                       | VoltagePlus™  |
| FETBench™   | OPTOPLANAR®                                     |                                       | XS™   |
| FPS™  |   |                                       |   |

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 166

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative